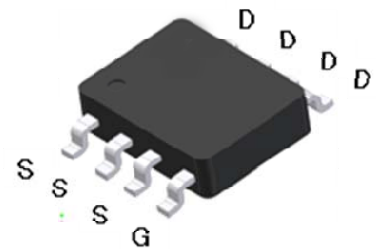


**N-Channel Logic Level Enhancement Mode Field Effect Transistor**

**Product Summary:**

|                            |       |
|----------------------------|-------|
| BV <sub>DSS</sub>          | 100V  |
| R <sub>DS(on)</sub> (MAX.) | 150mΩ |
| I <sub>D</sub>             | 4A    |



UIS, R<sub>g</sub> 100% Tested

Pb-Free Lead Plating & Halogen Free



**ABSOLUTE MAXIMUM RATINGS (T<sub>A</sub> = 25 °C Unless Otherwise Noted)**

| PARAMETERS/TEST CONDITIONS                     |                                                    | SYMBOL                            | LIMITS     | UNIT |
|------------------------------------------------|----------------------------------------------------|-----------------------------------|------------|------|
| Gate-Source Voltage                            |                                                    | V <sub>GS</sub>                   | ±20        | V    |
| Continuous Drain Current                       | T <sub>A</sub> = 25 °C                             | I <sub>D</sub>                    | 4          | A    |
|                                                | T <sub>A</sub> = 100 °C                            |                                   | 2.8        |      |
| Pulsed Drain Current <sup>1</sup>              |                                                    | I <sub>DM</sub>                   | 16         |      |
| Avalanche Current                              |                                                    | I <sub>AS</sub>                   | 4          | mJ   |
| Avalanche Energy                               | L = 0.1mH, I <sub>D</sub> =4A, R <sub>G</sub> =25Ω | E <sub>AS</sub>                   | 0.8        |      |
| Repetitive Avalanche Energy <sup>2</sup>       | L = 0.05mH                                         | E <sub>AR</sub>                   | 0.4        |      |
| Power Dissipation                              | T <sub>A</sub> = 25 °C                             | P <sub>D</sub>                    | 2.5        | W    |
|                                                | T <sub>A</sub> = 100 °C                            |                                   | 1          |      |
| Operating Junction & Storage Temperature Range |                                                    | T <sub>j</sub> , T <sub>stg</sub> | -55 to 150 | °C   |

**THERMAL RESISTANCE RATINGS**

| THERMAL RESISTANCE               | SYMBOL           | TYPICAL | MAXIMUM | UNIT   |
|----------------------------------|------------------|---------|---------|--------|
| Junction-to-Case                 | R <sub>θJC</sub> |         | 25      | °C / W |
| Junction-to-Ambient <sup>3</sup> | R <sub>θJA</sub> |         | 50      |        |

<sup>1</sup>Pulse width limited by maximum junction temperature.

<sup>2</sup>Duty cycle ≤ 1%

<sup>3</sup>50°C / W when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.

**ELECTRICAL CHARACTERISTICS ( $T_A = 25\text{ }^{\circ}\text{C}$ , Unless Otherwise Noted)**

| PARAMETER                                                               | SYMBOL        | TEST CONDITIONS                                               | LIMITS |      |           | UNIT       |
|-------------------------------------------------------------------------|---------------|---------------------------------------------------------------|--------|------|-----------|------------|
|                                                                         |               |                                                               | MIN    | TYP  | MAX       |            |
| STATIC                                                                  |               |                                                               |        |      |           |            |
| Drain-Source Breakdown Voltage                                          | $V_{(BR)DSS}$ | $V_{GS} = 0V, I_D = 250\mu A$                                 | 100    |      |           | V          |
| Gate Threshold Voltage                                                  | $V_{GS(th)}$  | $V_{DS} = V_{GS}, I_D = 250\mu A$                             | 1.0    | 2.0  | 3.0       |            |
| Gate-Body Leakage                                                       | $I_{GSS}$     | $V_{DS} = 0V, V_{GS} = \pm 20V$                               |        |      | $\pm 100$ | nA         |
| Zero Gate Voltage Drain Current                                         | $I_{DSS}$     | $V_{DS} = 80V, V_{GS} = 0V$                                   |        |      | 1         | $\mu A$    |
|                                                                         |               | $V_{DS} = 70V, V_{GS} = 0V, T_J = 125\text{ }^{\circ}C$       |        |      | 10        |            |
| On-State Drain Current <sup>1</sup>                                     | $I_{D(ON)}$   | $V_{DS} = 10V, V_{GS} = 10V$                                  | 4      |      |           | A          |
| Drain-Source On-State Resistance <sup>1</sup>                           | $R_{DS(ON)}$  | $V_{GS} = 10V, I_D = 2A$                                      |        | 125  | 150       | m $\Omega$ |
|                                                                         |               | $V_{GS} = 5V, I_D = 1.5A$                                     |        | 168  | 225       |            |
| Forward Transconductance <sup>1</sup>                                   | $g_{fs}$      | $V_{DS} = 5V, I_D = 2A$                                       |        | 8    |           | S          |
| DYNAMIC                                                                 |               |                                                               |        |      |           |            |
| Input Capacitance                                                       | $C_{iss}$     | $V_{GS} = 0V, V_{DS} = 20V, f = 1MHz$                         |        | 1030 |           | pF         |
| Output Capacitance                                                      | $C_{oss}$     |                                                               |        | 50   |           |            |
| Reverse Transfer Capacitance                                            | $C_{rss}$     |                                                               |        | 42   |           |            |
| Gate Resistance                                                         | $R_g$         | $V_{GS} = 15mV, V_{DS} = 0V, f = 1MHz$                        |        | 1.2  |           | $\Omega$   |
| Total Gate Charge <sup>1,2</sup>                                        | $Q_g$         | $V_{DS} = 80V, V_{GS} = 10V,$<br>$I_D = 2A$                   |        | 23   |           | nC         |
| Gate-Source Charge <sup>1,2</sup>                                       | $Q_{gs}$      |                                                               |        | 2.3  |           |            |
| Gate-Drain Charge <sup>1,2</sup>                                        | $Q_{gd}$      |                                                               |        | 6.1  |           |            |
| Turn-On Delay Time <sup>1,2</sup>                                       | $t_{d(on)}$   | $V_{DS} = 50V,$<br>$I_D = 1A, V_{GS} = 10V, R_{GS} = 6\Omega$ |        | 12   |           | nS         |
| Rise Time <sup>1,2</sup>                                                | $t_r$         |                                                               |        | 20   |           |            |
| Turn-Off Delay Time <sup>1,2</sup>                                      | $t_{d(off)}$  |                                                               |        | 25   |           |            |
| Fall Time <sup>1,2</sup>                                                | $t_f$         |                                                               |        | 25   |           |            |
| SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T <sub>c</sub> = 25 °C) |               |                                                               |        |      |           |            |
| Continuous Current                                                      | $I_S$         |                                                               |        |      | 2.3       | A          |
| Pulsed Current <sup>3</sup>                                             | $I_{SM}$      |                                                               |        |      | 9.2       |            |
| Forward Voltage <sup>1</sup>                                            | $V_{SD}$      | $I_F = I_S, V_{GS} = 0V$                                      |        |      | 1.2       | V          |
| Reverse Recovery Time                                                   | $t_{rr}$      | $I_F = I_S, di_F/dt = 100A / \mu S$                           |        | 35   |           | nS         |
| Reverse Recovery Charge                                                 | $Q_{rr}$      |                                                               |        | 65   |           | nC         |

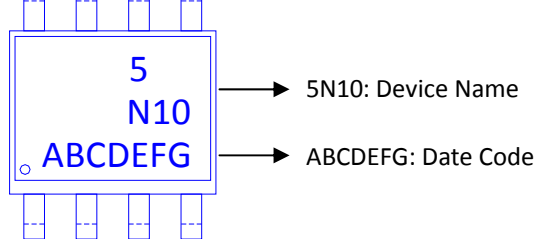
<sup>1</sup>Pulse test : Pulse Width  $\leq 300\text{ }\mu\text{sec}$ , Duty Cycle  $\leq 2\%$ .

<sup>2</sup>Independent of operating temperature.

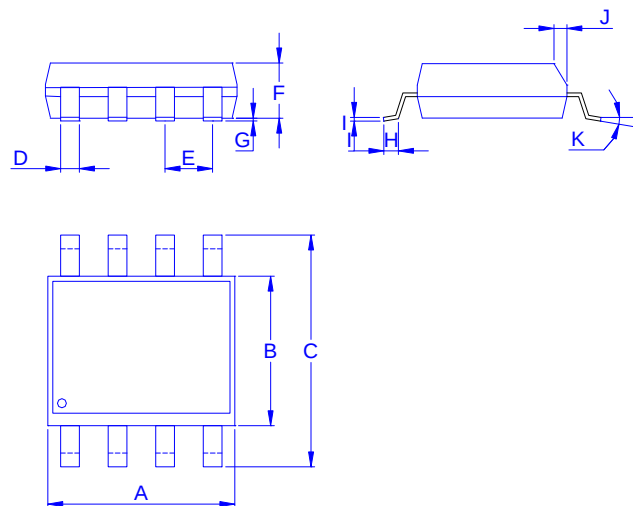
<sup>3</sup>Pulse width limited by maximum junction temperature.

## Ordering & Marking Information:

Device Name: LB5N10H for SOP-8



## Outline Drawing



Dimension in mm

| Dimension | A    | B    | C    | D    | E    | F    | G    | H    | I    | J    | K  |
|-----------|------|------|------|------|------|------|------|------|------|------|----|
| Min.      | 4.70 | 3.70 | 5.80 | 0.33 |      | 1.20 | 0.08 | 0.40 | 0.19 | 0.25 | 0° |
| Typ.      |      |      |      |      | 1.27 |      |      |      |      |      |    |
| Max.      | 5.10 | 4.10 | 6.20 | 0.51 |      | 1.62 | 0.28 | 0.83 | 0.26 | 0.50 | 8° |

TYPICAL CHARACTERISTICS

